

Spin-dependent Andreev reflection tunneling through a quantum dot with intradot spin- $\uparrow\downarrow$ scattering

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Abstract

We study Andreev reflection (AR) tunneling through a quantum dot (QD) connected to a ferromagnet and a superconductor, in which the intradot spin- $\uparrow\downarrow$ interaction is included. By using the nonequilibrium Green-function method, the formula of the linear AR conductance is derived at zero temperature. It is found that competition between the intradot spin- $\uparrow\downarrow$ scattering and the tunneling coupling to the leads dominates resonant behaviours of the AR conductance versus the gate voltage. A weak spin- $\uparrow\downarrow$ scattering leads to a single peak resonance. However, with the spin- $\uparrow\downarrow$ scattering strength increasing, the AR conductance will develop into a double peak resonance implying a novel structure in the tunneling spectrum of the AR conductance. Besides, the effect of the spin-dependent tunneling couplings, the matching of Fermi velocity, and the spin polarization of the ferromagnet on the AR conductance is examined in detail.

Key word: Spin- $\uparrow\downarrow$ interaction, Andreev reflection, spin polarization

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1. Introduction

With the advances of nanofabrication and material growth technologies, it has been possible to realize various kinds of hybrid mesoscopic structures¹⁻⁴. Recently, spin-dependent electronic transport through these hybrid mesoscopic structures has become one of the major focuses of the rapidly developing spintronics⁵ for both its fundamental physics and potential applications. In particular, the Andreev reflection (AR) in spin-polarized transport through ferromagnet-superconductor (F-S) junctions has been examined based on the scattering matrix formulation^{6,11}. It is found that in the case of low bias voltage, AR tunneling at the F-S interface is strongly affected by the spin polarization of the ferromagnet side⁶ and the measuring of the differential AR conductance can successfully determine the spin polarization at the Fermi energy for several metals⁷. In addition, further calculations^{8,9} showed that the AR conductance of F-S junction is also modified by the Fermi velocity mismatch, and it may even appear a peak with the varying of spin polarization of the ferromagnet.

On the other hand, spin-dependent resonant tunneling through a quantum dot (QD), a small system characterized by discrete electronic states, coupled a ferromagnet (F) and a superconductor (S) leads has been another interesting subject of experimental and theoretical investigations for the past decade. Zhu¹² et al. proposed an efficient mechanism for the operation of writing spin in such the F-QD-S system with the principle of the Andreev reflection induced spin polarization. They¹³ also studied the AR tunneling through a QD with two ferromagnets and a superconductor, in which only one spin-degenerate level of the QD is considered and the intradot Coulomb interaction is ignored. In this three terminal hybrid structure, the transport conducted by crossed AR, which involves an incident electron with spin from one of the ferromagnets picks up another electron with the opposed spin from the other one, both enter the S-lead and form a Cooper pair, is particularly interesting. It is found that the AR tunneling processes are, besides the spin polarizations and the matching condition of Fermi velocity, strongly dependent on the tilt angle between the magnetization orientations of the two F-leads. Feng and Xiong¹⁴ investigated the transport properties of a F-QD-S system, in which both the Coulomb interaction and the multilevel structure of

the QD are considered. However, the spin- $\uparrow\downarrow$ scattering is only included in the tunneling barriers.

Meanwhile, the significant role of spin-orbit interaction in the QD, which may cause the spin rotation of an electron while in the QD, has attracted considerable attentions more recently¹⁵, especially in spin-polarized transport in magnetic nanostructures^{16,19}. The spin- $\uparrow\downarrow$ mechanisms in the GaAs-based QD have been investigated in Ref.[15]. Most of the theoretical studies^{17,19} concentrate on exploring the effect of the intradot spin- $\uparrow\downarrow$ scattering on linear and nonlinear conductances of F-QD-F systems in Kondo regime and a wide variety of novel features have been revealed. When the spin- $\uparrow\downarrow$ scattering strength is of the order of the Kondo temperature, the original single Kondo peak in the differential conductance is split into two peak or three peak structure due to the spin- $\uparrow\downarrow$ process in the QD^{18,19}. Hence, it is natural to ask if the intradot spin- $\uparrow\downarrow$ scattering could induce some novel spectrum of tunneling AR conductance in the F-QD-S system.

In this paper we study the AR tunneling through a F-QD-S hybrid structure by using nonequilibrium Green Function method. We mainly emphasize the effect of the spin- $\uparrow\downarrow$ scattering in the QD on linear AR conductance at zero temperature. Until now to our knowledge, there are no theoretical research works to examine this issue. The spin- $\uparrow\downarrow$ scattering in the QD plays important roles for the AR process of such a F-QD-S system. For an isolated QD, it can split one spin-degenerate level of the QD, ϵ_d , to two spin-coherent levels, $\epsilon_{\pm} = \epsilon_d \pm R$, whose states are a superposition of the spin-up and spin-down ones. It implicates¹⁷ that incident electrons with up-spin and down-spin from the left F-lead should tunnel coherently into the levels split by the intradot spin- $\uparrow\downarrow$ scattering. In the spin-coherent tunneling process, it is expected for the Andreev reflection to bring about some novel resonant features of the conductance. We found that the competition between the level splitting and the broadening of the split levels arisen from the tunneling coupling, together with the spin polarization and the Fermi velocity matching condition, can determine the spin-up and spin-down populations of the QD, and further dominates resonant behaviors of

the AR conductance of the system. When the spin- $\uparrow\downarrow$ scattering strength overbears that of the tunneling coupling to the leads, the AR conductance versus the gate voltage displays a symmetric double peak resonance, and the spin- $\uparrow\downarrow$ scattering always suppresses the heights of the double peaks. However, for a weak spin- $\uparrow\downarrow$ scattering process in the QD, it only leads to a single peak resonance of the AR conductance. In this case, as the spin- $\uparrow\downarrow$ scattering strength increases, the height of the conductance peak may be first increased gradually and then dropped, depending the matching condition of the Fermi velocity.

2. The model and formulas

Consider resonant AR tunneling through a QD with the intradot spin- $\uparrow\downarrow$ scattering connected to a F-lead and a S-lead, in which only one spin degenerate energy level is included and the Coulomb repulsion is ignored for simplicity. The spin quantization axis of the F-QD-S system is taken as the direction of the F-lead magnetization, along z-axis. The model is shown schematically in Fig.1. The Hamiltonian of the system under consideration, can be written as

$$H = H_F + H_S + H_{\text{dot}} + H_T \quad (1)$$

with

$$H_F = \sum_{k\uparrow} (\epsilon_k + M) f_k^\dagger f_k \quad (2)$$

$$H_S = \sum_{p\uparrow} \epsilon_p s_p^\dagger s_p + \sum_p (\epsilon_p s_{p\uparrow}^\dagger s_{p\downarrow} + s_{p\downarrow}^\dagger s_{p\uparrow}) \quad (3)$$

$$H_{\text{dot}} = \epsilon_d d^\dagger d + R (d_{\uparrow}^\dagger d_{\downarrow} + d_{\downarrow}^\dagger d_{\uparrow}) \quad (4)$$

$$H_T = \sum_{k\uparrow} (T_k f_k^\dagger d + H.c.) + \sum_{p\downarrow} (T_p s_p^\dagger d + H.c.) \quad (5)$$

where H_F and H_S are the Hamiltonians for the F-lead and the S-lead, respectively. Under mean-field approximation, the F-lead is characterized by a molecular magnetic moment M .

The angle between molecular magnetic moment and the F-QD interface is chosen to be zero. The BCS Hamiltonian is adopted for the S-lead with an order parameter standing for its energy gap. H_{dot} models the QD with single spin degenerate level ϵ_d . The spin-orbit term in the H_{dot} is caused by spin-orbit interaction in the QD^{15;17} and R is the spin-orbit scattering strength. H_T describes the tunneling part between the QD and the F-lead and the S-lead with the tunneling matrixes T_k and T_p . The spin conservation is assumed in the tunneling barrier processes, which is distinguished from that in Ref. [14].

The current flowing into the central region from the left ferromagnetic lead can be evaluated from the time evaluation of the total electron number in the left lead^{13;20}:

$$J_1 = -e\hbar \frac{dN_1(t)}{dt} = \frac{e}{h} \text{Re} \sum_k \sum_{\sigma} T_{k,\sigma}^Y G_{k,\sigma}^<(t;t) \quad (6)$$

Here various kinds of Green functions are expressed in 4 × 4 Nambu representation²⁰. The Green's functions of the electron of the QD can be exactly solved in the terms of Dyson's equation, $G^{r;a} = g^{r;a} + g^{r;a} \Sigma^{P,r;a} G^{r;a}$, in which $\Sigma^{P,r;a}$ is the self-energy due to both the spin-orbit interaction in the QD and the spin-dependent tunneling couplings to the left and right leads, and $g^{r;a}$ is the Green function without both the tunneling coupling and the intradot spin-orbit scattering:

$$(g^{r;a})^{-1} = \begin{pmatrix} 0 & 0 & 0 & 0 \\ \vdots & \epsilon_d - i0^+ & 0 & 0 \\ 0 & 0 & \epsilon_d - i0^+ & 0 \\ 0 & 0 & 0 & \epsilon_d - i0^+ \end{pmatrix} \quad (7)$$

For the F-QD-S system studied, $\Sigma^{P,r;a}$ can be written as $\Sigma^{P,r;a} = \Sigma_R^P + \Sigma_{f0}^{P,r;a} + \Sigma_{s0}^{P,r;a}$. Here the off-diagonal term of H_{dot} , the intradot spin-orbit scattering, is conveniently considered by the self-energy Σ_R^P :

$$\Sigma_R^P = \begin{pmatrix} 0 & 0 \\ \vdots & 0 \\ 0 & 0 \\ \vdots & 0 \end{pmatrix} \begin{pmatrix} 0 & R & 0 & 0 \\ 0 & 0 & 0 & R \\ 0 & 0 & 0 & 0 \\ 0 & R & 0 & 0 \end{pmatrix} \quad (8)$$

$$f = f_0 \begin{pmatrix} 0 & 0 & 0 & 0 \\ (1 + P) & 0 & 0 & 0 \\ 0 & (1 - P) & 0 & 0 \\ 0 & 0 & (1 - P) & 0 \\ 0 & 0 & 0 & (1 + P) \end{pmatrix} \quad (9)$$
$$r_s^a = \frac{i}{2} r_s (!) \begin{pmatrix} 0 & 1 \\ 1 & 0 \\ 0 & 0 \\ 0 & 0 \end{pmatrix} \quad (10)$$
$$\frac{r}{s}(!) = \frac{j! j (j! j)}{1! 2} + \frac{j! j (j! j)}{1! 2} \quad (11)$$
$$s = \begin{pmatrix} 0 & 1 \\ 1 & 0 \end{pmatrix} \quad (12)$$

with $\langle \sigma \rangle = \frac{1}{2} \left(\langle \sigma_z \rangle + \langle \sigma_x \rangle \right) = \frac{1}{2} \left(\frac{1}{2} + \frac{1}{2} \right) = \frac{1}{2}$. After a straightforward calculation, we obtain the formula of the tunneling current as follows:

$$J = J_N + J_A \quad (13)$$

with

$$J_N = \frac{e^2}{h} \sum_{i=1,3} \left[f_L(\epsilon_i - eV) - f_R(\epsilon_i) \right] \sum_{j=1,3} G_{d,i;j}^r G_{d,f;j}^a \quad (14)$$

and

$$J_A = \frac{e^2}{h} \sum_{i=1,3} \left[f_L(\epsilon_i - eV) - f_L(\epsilon_i + eV) \right] \sum_{j=1,3} G_{d,i;j}^r (f_R G_{d,f;j}^a - f_L G_{d,f;j}^a) \quad (15)$$

where f_L and f_R are the Fermi-distribution functions in the left and right leads, respectively. J_N is the normal tunneling current which is caused by the single quasiparticle or quasihole transport, and J_A is the Andreev refection current. In the linear response regime, the normal tunneling conductance and the AR conductance are obtained as follows:

$$G_N = \frac{e^2}{h} \sum_{i=1,3} \left[\frac{\partial f}{\partial \epsilon} \right] \sum_{j=1,3} G_{d,i;j}^r G_{d,f;j}^a \quad (16)$$

and

$$G_A = \frac{2e^2}{h} \sum_{i=1,3} \left[\frac{\partial f}{\partial \epsilon} \right] \sum_{j=1,3} G_{d,i;j}^r (f_R G_{d,f;j}^a - f_L G_{d,f;j}^a) \quad (17)$$

Since the normal linear conductance is zero, $G_N = 0$, at zero temperature, only the Andreev refection process contributes to the linear electronic transport of the system. So the total conductance G is equivalent to G_A .

3. The calculated results and discussion

We constrain ourselves only to discuss linear AR conductance at zero temperature for the F-QD-S, in which the energy level of the QD ϵ_d , controlled by the gate voltage V_g , is restricted in the range of the energy gap of the S-lead ($|\epsilon_d| < \Delta$) and $|\epsilon_d - \epsilon_F| < \Delta$. In the following calculation, both Fermi energies of the F- and S-leads are set to zero, the energy gap of the S-lead, Δ , is taken as energy unit and the spin polarization is chosen as $P = 0.3$.

First we illustrate the effect of the intradot spin- $\uparrow\downarrow$ scattering on resonant behaviors of the AR conductance versus the energy level of the QD, ϵ_d . In Fig 2, let $\epsilon_{s0} = 0.1$, we plotted the AR conductance as a function of ϵ_d in Fig 2 (a) with $\epsilon_{f0} = 0.02$, Fig 2 (b) $\epsilon_{f0} = 0.1$, and Fig 2 (c) $\epsilon_{f0} = 0.2$, for some different spin- $\uparrow\downarrow$ scattering strengths, $R = 0$ (solid line), 0.03 (dashed line), 0.05 (dotted line), 0.07 (dot-dashed line), 0.09 (dot-dot-dashed line), and 0.15 (short dashed line), respectively. In Fig 2 (a), $\epsilon_{f0} < \epsilon_{s0}$, it is clearly seen that for a weak spin- $\uparrow\downarrow$ scattering in the range of $R = 0 \sim 0.05$, the AR conductance displays a single peak resonance at the position of $\epsilon_d = 0$ and its amplitude gradually rises till the maximum $G_m = 4e^2/h$, at $R_m = \epsilon_{s0}/2 = 0.05$, with the R increasing. This is a perfect AR tunneling process. For some stronger spin- $\uparrow\downarrow$ scatterings $R (0.05 \sim 0.06)$, however, the AR conductance displays also a single peak profile at $\epsilon_d = 0$, but the amplitude of the resonant peak reduces quickly. As the spin- $\uparrow\downarrow$ scattering further increases, $R > 0.06$, the original single peak of the conductance develops to a well-resolved double peak resonance. The peaks appear near by $\pm R$, respectively. Furthermore, the intradot spin- $\uparrow\downarrow$ scattering always suppresses the heights of the resonant double peaks.

Fig. 2 (b) presents some curves of the resonant AR conductance for the symmetric tunneling couplings, $\epsilon_{f0} = \epsilon_{s0} = 0.1$, and other parameters are the same as those in Fig. 2 (a). Comparing with Fig. 2 (a), a strong enough spin- $\uparrow\downarrow$ scattering $R (> 0.08)$ brings about a double peak resonance of the conductance due to the larger broadening of two split levels $\epsilon_{\pm} = (\epsilon_{f0} \pm \epsilon_{s0})$. It is found that the widths of the resonant double peaks enlarges for the enhanced broadening of the minority spin, $\epsilon_{\#}$. In Fig 2 (c), $\epsilon_{f0} > \epsilon_{s0}$, the amplitude of the single peak resonance shows a novel feature: as the spin- $\uparrow\downarrow$ scattering increases, the peak amplitude of the resonance is decreased monotonously. It is worth to notice that in the presence of the intradot spin- $\uparrow\downarrow$ scattering, the single peak of the AR conductance exhibits characteristic behaviors essentially depending on a effective overlap of the broadening of the two split levels.

To elucidate the evolution of the resonant AR conductance from single peak to double peaks, we calculate the magnitude of the AR conductance at $\epsilon_d = 0$, G_0 , versus the spin-

ip scattering strength R . Defining the ratio of the two tunneling coupling strengths $r = \Gamma_{S0} / \Gamma_{F0}$, the matching condition of the Fermi velocity, $v_F = v_{F\#} = \frac{2}{s_0}$ reads now as $P^2 + r^2 = 1$. Fig. 3 (a) shows some curves of the AR conductance G_0 , for a given $s_0 = 0.1$ and several different $\Gamma_{F0} = 0.1$ (solid line), $0.1=3$ (dashed line), $0.1=5$ (dotted line), $0.1=7$ (dot-dashed line), $0.1=9$ (dot-dot-dashed line). For the case of $r > 1$, the magnitude of G_0 increases firstly to its maximum $4e^2/h$ at R_m and then drops fastly as the spin-ip scattering strength R increases. It should be mentioned that for the $r > 1$ where the matching of the Fermi velocity can never be satisfied, G_0 should decrease monotonously with the spin polarization P increasing and can not reach to the maximum $4e^2/h$ ^{13,14}. Our calculations indicated that there must exist, apart from what considered in Ref.[3] and [14], some other mechanisms that result in the perfect AR tunneling, G_0 rising to $4e^2/h$. We believe the intradot spin-ip scattering may account for it and leaving somewhat discussion in later. For a enough small Γ_{F0} , G_0 becomes a very sharp peak, and its maximum position R_m approaches very closely to $R = s_0=2$. This means that if the spin-ip scattering strength slightly deviates from $s_0=2$, the AR conductance quickly decreases from $4e^2/h$ to 0.

The typical feature showed in Fig 3 (a) is understood qualitatively as follows. Spin-up and spin-down electrons can escape from the QD through the tunneling coupling to the leads, which leads to finite resonant broadening of the two spin-coherent split levels ($\Gamma_d = \Gamma$) by an amount Γ . Here $\Gamma = \Gamma_{S0} + \Gamma_F + \Gamma_{F\#} = (\Gamma_{S0} + 2\Gamma_{F0})$, the linewidth of the split levels, delineates the distribution of the density of states (DOS), in which Γ_F and $\Gamma_{F\#}$ are spin-dependent tunneling rates to the F-side. Γ_{S0} is spin-independent tunneling rate to the S-side. When $R < R_m$ ($s_0=2$), the linewidths of the two split levels are overlapped effectively at $\Gamma_d = 0$, so that the AR conductance versus Γ_d behaves as single peak resonance. In this situation, the AR conductance G_0 , is enhanced with increasing R , because the intradot spin-ip scattering not only shift the level position of the QD from $\Gamma_d = 0$ to $\Gamma_d = R$, but also change the spin-up and spin-down distribution of the DOS for the split levels¹⁷. Since the minority spin population near the Fermi energy determines behaviors of the AR tunneling, the spin-ip scattering turns effectively the majority spin carriers to minority

ones near $\epsilon_d = 0$ resulting in G_0 to rise till its maximum $4e^2/h$, at R_m , in which spin-up and spin-down carriers from the F-lead completely form pairs into the S-lead. When $R > s_0 = 2 + f_0 > R_m$, the two split levels have been shifted sufficiently away from each other leaving a vanishing spin-dependent DOS at $\epsilon_d = 0$. Therefore G_0 drops quickly to zero and it should appear a deep valley in the resonant conductance curve. This implies that the AR conductance has developed into a well-resolved double peak resonance shown in Fig. 2 (a). Fig. 3 (b) presents the curves of the AR conductance, G_0 versus R with a fixed $f_0 = 0.1$ and several different s_0 , for $r > 1$. The peaks exist at a larger R_m than that in Fig. 3 (a) owing to the stronger tunneling coupling rate s_0 , but their patterns are very analogous to each other due to the same spin minority $f_{\#}$.

In Fig. 4 (a), we plotted G_0 as a function of the spin- $\uparrow\downarrow$ scattering strength R with a fixed $s_0 = 0.1$ and several different $f_0 = 0.1$ (solid line), 0.3 (dashed line), 0.5 (dotted line), 0.7 (dot-dashed line), 0.9 (dot-dot-dashed line). This is the situation of $r < 1$, and the magnitude of G_0 decreases monotonously with R increasing. Since the linewidths Γ_{\uparrow} and $\Gamma_{\#}$ are much larger than s_0 , the spin-up and spin-down DOS are comparatively low. With the increasing of spin- $\uparrow\downarrow$ scattering, the minority spin occupation reduces gradually at $\epsilon_d = 0$. Simultaneously, majority spin carriers can scarcely turn to minority ones near $\epsilon_d = 0$ because of the requirement of the energy conservation. As a result, the magnitude of G_0 decreases monotonously with the R increasing. In Fig. 4 (b), we present some curves of G_0 for the case of $r < 1$ with a fixed $f_0 = 0.1$, but for several different s_0 . Similar features, but a even faster drop of G_0 with R as in Fig. 4 (a), have been indicated. As is well-known, s_0 describes the probability that two electrons in the QD tunnel into the S-lead and form a Cooper pair. So the weaker the s_0 , the less the probability, and the faster does the G_0 decrease to zero as the R increases.

4. Conclusion

In summary, we have studied the spin-dependent AR tunneling through a F-QD-S structure by using nonequilibrium Green function method. We found that the coherent spin- $\uparrow\downarrow$ scattering in the QD plays important roles in the spin-dependent AR tunneling through the

F-QD-S system. The observed single or double peak resonant behaviors of the AR conductance, versus the gate voltage, is a consequence of the competition between the spin-ip scattering and the resonant broadenings of the two split levels due to the tunneling coupling to the leads. When the spin-ip scattering strength in the QD is smaller than the broadenings of the split levels, the AR conductance exhibits a single peak resonances. In this case, as the spin-ip scattering strength increases, the height of the single peak conductance may be first increased gradually and then deduced dropped quickly. However, when the spin-ip scattering induced splitting of the spin-degenerate level overbears the broadening of the split levels, the AR conductance appears as a symmetric double peak resonance, for which a novel structure in the tunneling spectrum of the AR conductance is predicted to appear. We expect the present results may have practical applications in the field of spintronics.

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FIGURES

Fig1. The quantum dot with intradot spin-orbit interaction is coupled to a ferromagnet and a superconductor. A level of the QD is split into two spin coherent levels by the spin- $\uparrow\downarrow$ interaction.

Fig2. The resonant curves of the AR conductance versus the energy level of the QD, ϵ_d , with parameters $P = 0.3$, $s_0 = 0.1$ and several spin- $\uparrow\downarrow$ scattering strengths $R = 0$ (solid line), 0.03 (dashed line), 0.05 (dotted line), 0.07 (dot-dashed line), 0.09 (dot-dot-dashed line), and 0.15 (short dashed line) for three different spin-averaged tunneling couplings to the F-lead: (a) $\epsilon_0 = 0.02$, $\epsilon_0 < s_0$, (b) $\epsilon_0 = 0.1$, $\epsilon_0 = s_0$, and $\epsilon_0 = 0.2$, $\epsilon_0 > s_0$.

Fig3. The AR conductance at $\epsilon_d = 0$, G_0 versus the R with a parameter $P = 0.3$ (a). $\epsilon_0 < s_0$ and $s_0 = 0.1$, the curves of the conductance for some different $\epsilon_0 = 0.1$ (solid line), $0.1=3$ (dashed line), $0.1=5$ (dotted line), $0.1=7$ (dot-dashed line), $0.1=9$ (dot-dot-dashed line). (b). $\epsilon_0 < s_0$ and $\epsilon_0 = 0.1$, the curves of the conductance for $s_0 = 0.1$ (solid line), 0.3 (dashed line), 0.5 (dotted line), 0.7 (dot-dashed line), 0.9 (dot-dot-dashed line).

Fig4 The G_0 versus R with a parameter $P = 0.3$, $\epsilon_0 > s_0$ (a). $s_0 = 0.1$, the curves of the conductance for some different $\epsilon_0 = 0.1$ (solid line), 0.3 (dashed line), 0.5 (dotted line), 0.7 (dot-dashed line), 0.9 (dot-dot-dashed line). (b). $\epsilon_0 = 0.1$, the curves of the conductance for $s_0 = 0.1$ (solid line), $0.1=3$ (dashed line), $0.1=5$ (dotted line), $0.1=7$ (dot-dashed line), $0.1=9$ (dot-dot-dashed line).

Fig. 1

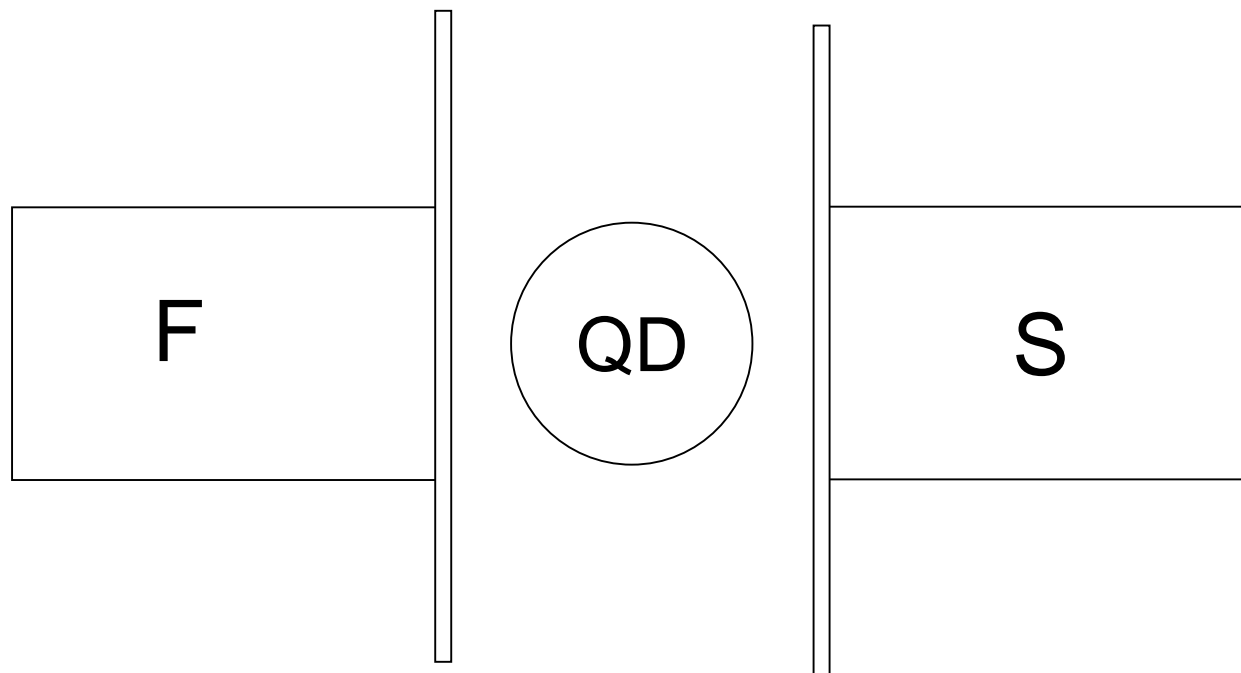


Fig. 2

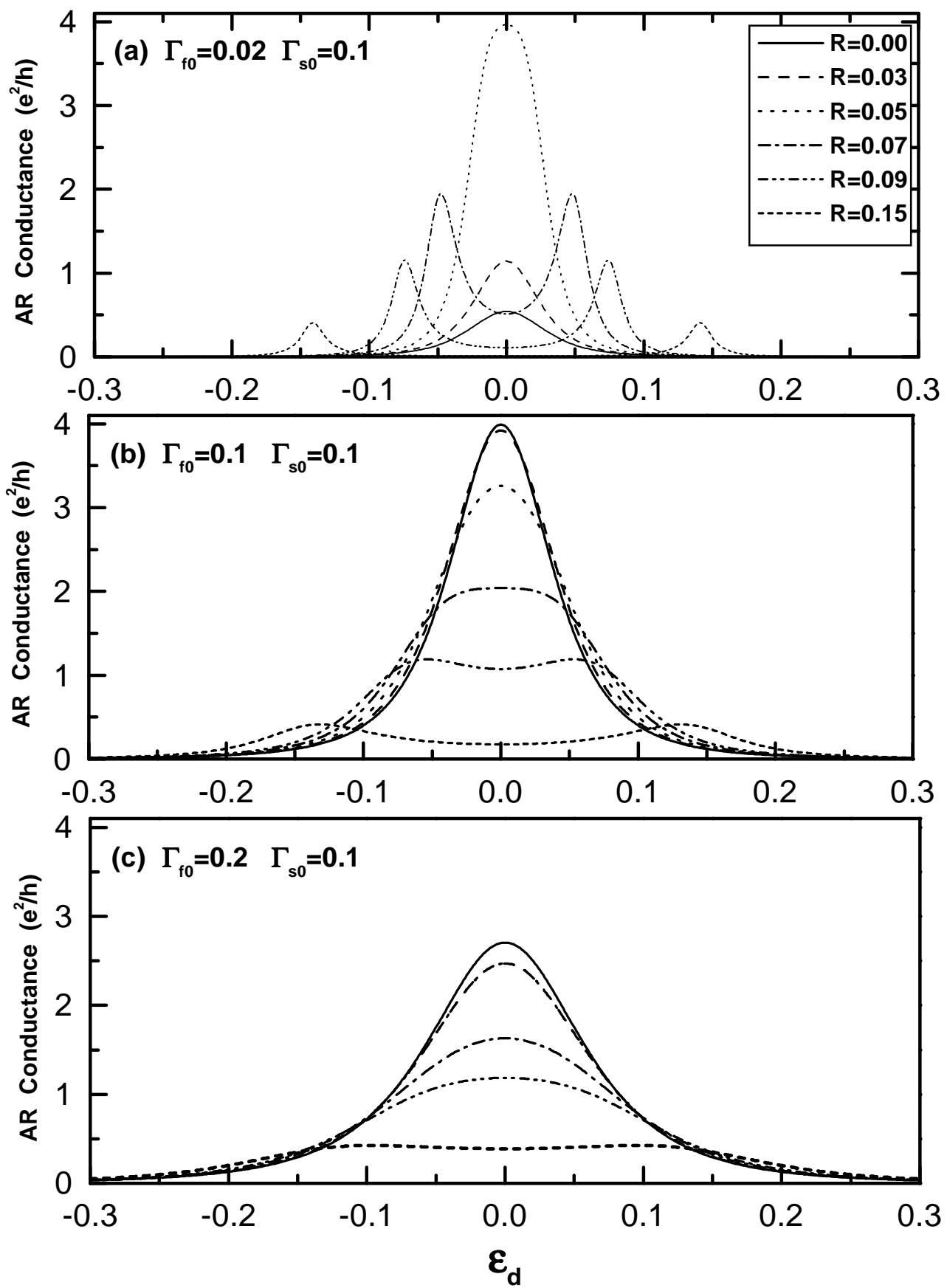


Fig. 3

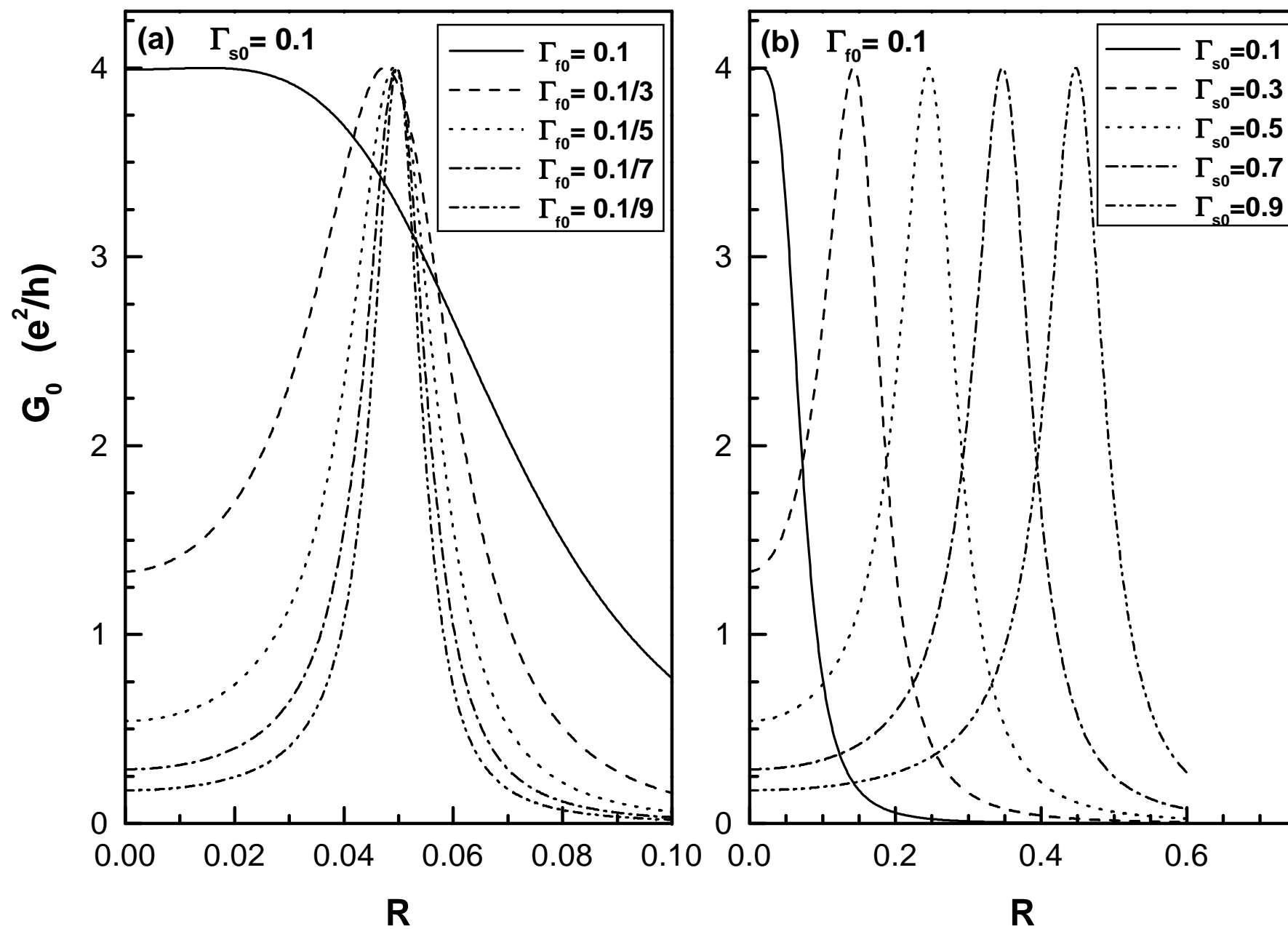


Fig. 4

